

MOSFETs Silicon P-Channel MOS (U-MOSVI)

SSM3J356R

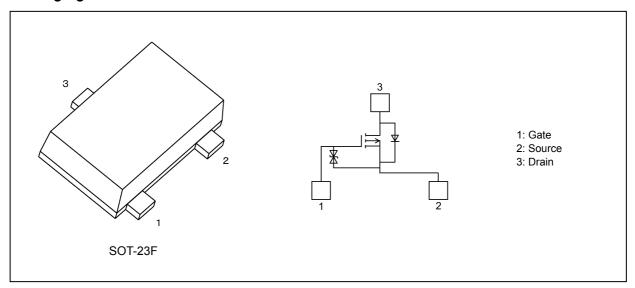
1. Applications

· Power Management Switches

2. Features

- (1) AEC-Q101 qualified (Please see the orderable part number list)
- (2) 4 V gate drive voltage.
- (3) Low drain-source on-resistance
 - : $R_{DS(ON)} = 400 \text{ m}\Omega \text{ (max) } (@V_{GS} = -4.0 \text{ V})$ $R_{DS(ON)} = 300 \text{ m}\Omega \text{ (max) } (@V_{GS} = -10 \text{ V})$

3. Packaging and Internal Circuit



4. Orderable part number

| Orderable part number | AEC-Q101 | | Note | | |
|-----------------------|----------|----------|----------------|----------|--|
| SSM3J356R,LF | _ | | General Use | | |
| SSM3J356R,LXGF | YES | (Note 1) | Unintended Use | (Note 1) | |
| SSM3J356R,LXHF | YES | | Automotive Use | | |

Note 1: For more information, please contact our sales or use the inquiry form on our website.



5. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

| | Characteristics | | | Symbol | Rating | Unit |
|------------------------|-----------------|-------|--------------------|------------------|------------|------|
| Drain-source voltage | | | | V_{DSS} | -60 | V |
| Gate-source voltage | | | | V_{GSS} | -20/+10 | |
| Drain current (DC) | | | (Note 1) | I_D | -2 | Α |
| Drain current (pulsed) | | | (Note 1), (Note 2) | I_{DP} | -6 | |
| Power dissipation | | | (Note 3) | P_{D} | 1 | W |
| Power dissipation | (t ≤ | 10 s) | (Note 3) | | 2 | |
| Channel temperature | | | | T_ch | 150 | ç |
| Storage temperature | | | | T _{stg} | -55 to 150 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Repetitive rating; pulse width limited by maximum channel temperature.
- Note 3: Device mounted on a 25.4 mm \times 25.4 mm \times 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm²)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R_{th(ch-a)}, and the drain power dissipation, P_D, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

6. Thermal Characteristics

| Characteristics | | Symbol | Max | Unit |
|---------------------------------------|----------|-----------------------|-----|------|
| Channel-to-ambient thermal resistance | (Note 1) | R _{th(ch-a)} | 125 | °C/W |

Note 1: Device mounted on an 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm²)



7. Electrical Characteristics

7.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------|----------------------|--|------|------|------|------|
| Gate leakage current | | I _{GSS} | V _{GS} = -16 V/+10 V, V _{DS} = 0 V | _ | _ | ±10 | μА |
| Drain cut-off current | | I _{DSS} | V _{DS} = -60 V, V _{GS} = 0 V | _ | _ | -10 | μА |
| Drain-source breakdown voltage | | V _{(BR)DSS} | $I_D = -1 \text{ mA}, V_{GS} = 0 \text{ V}$ | -60 | _ | _ | V |
| Drain-source breakdown voltage | (Note 1) | V _{(BR)DSX} | $I_D = -1 \text{ mA}, V_{GS} = 10 \text{ V}$ | -50 | _ | _ | |
| Gate threshold voltage | (Note 2) | V _{th} | V_{DS} = -10 V, I_{D} = -1 mA | -0.8 | _ | -2.0 | V |
| Drain-source on-resistance | (Note 3) | R _{DS(ON)} | $I_D = -1.0 \text{ A}, V_{GS} = -4.0 \text{ V}$ | _ | 280 | 400 | mΩ |
| | | | $I_D = -1.0 \text{ A}, V_{GS} = -4.5 \text{ V}$ | _ | 270 | 360 | |
| | | | I _D = -1.0 A, V _{GS} = -10 V | _ | 240 | 300 | |
| Forward transfer admittance | (Note 3) | Y _{fs} | V _{DS} = -10 V, I _D = -1 A | _ | 4.7 | _ | S |

Note 1: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (-1 mA for this device). Then, for normal switching operation, $V_{GS(ON)}$ must be higher than V_{th} , and $V_{GS(OFF)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$.

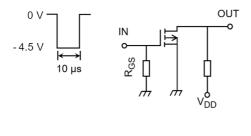
Take this into consideration when using the device.

Note 3: Pulse measurement.

7.2. Dynamic Characteristics (Unless otherwise specified, T_a = 25 °C)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance | C _{iss} | V _{DS} = -10 V, V _{GS} = 0 V, | _ | 330 | _ | pF |
| Reverse transfer capacitance | C _{rss} | f = 1 MHz | _ | 25 | _ | |
| Output capacitance | C _{oss} | | _ | 40 | _ | |
| Switching time (turn-on time) | t _{on} | V_{DD} = -30 V, I_{D} = -1.0 A V_{GS} = 0 to -4.5 V, R_{GS} = 10 Ω | | 29 | _ | ns |
| Switching time (turn-off time) | t _{off} | Duty \leq 1 %, V_{IN} : t_r , t_f < 5 ns, Common source, See Chapter 7.3. | _ | 48 | _ | |

7.3. Switching Time Test Circuit



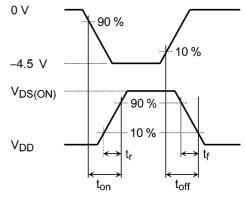


Fig. 7.3.1 Switching Time Test Circuit

Fig. 7.3.2 Input Waveform/Output Waveform

7.4. Gate Charge Characteristics (Unless otherwise specified, T_a = 25 °C)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | | $V_{DD} = -48 \text{ V}, V_{GS} = -10 \text{ V},$ | _ | 8.3 | | nC |
| Gate-source charge 1 | Q _{gs1} | I _D = -2.0 A | _ | 0.8 | | |
| Gate-drain charge | Q _{gd} | | _ | 1.7 | | |

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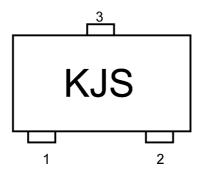


7.5. Source-Drain Characteristics (Unless otherwise specified, Ta = 25 °C)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-----------------------|----------|-----------|----------------------------------|-----|------|-----|------|
| Diode forward voltage | (Note 1) | V_{DSF} | I_{DR} = 2.0 A, V_{GS} = 0 V | | 0.9 | 1.2 | V |

Note 1: Pulse measurement.

8. Marking





9. Characteristics Curves (Note)

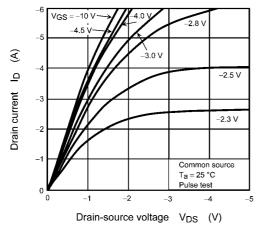


Fig. 9.1 I_D - V_{DS}

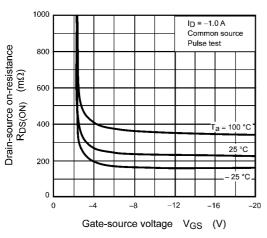


Fig. 9.3 R_{DS(ON)} - V_{GS}

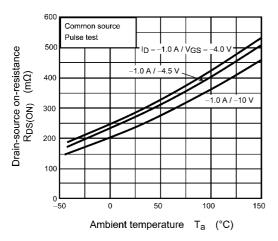


Fig. 9.5 R_{DS(ON)} - T_a

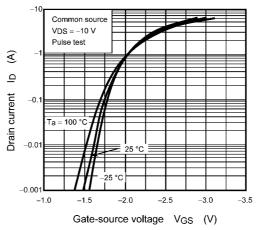


Fig. 9.2 I_D - V_{GS}

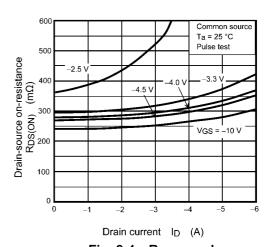


Fig. 9.4 R_{DS(ON)} - I_D

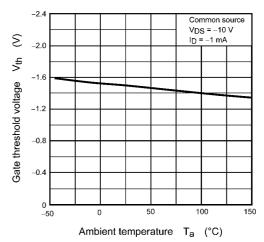


Fig. 9.6 V_{th} - T_a



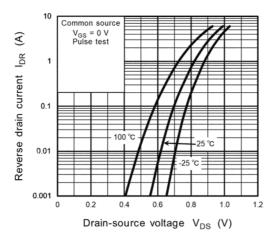


Fig. 9.7 IDR - VDS

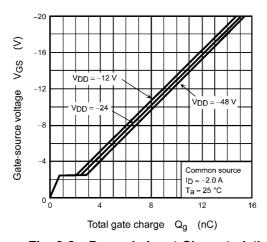


Fig. 9.9 Dynamic Input Characteristics

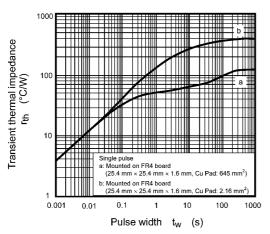


Fig. 9.11 rth - tw

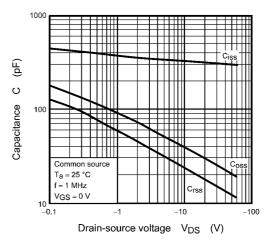


Fig. 9.8 C - V_{DS}

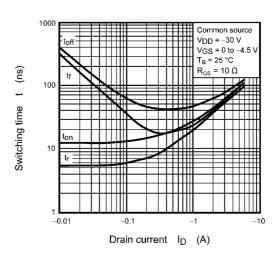


Fig. 9.10 t - I_D

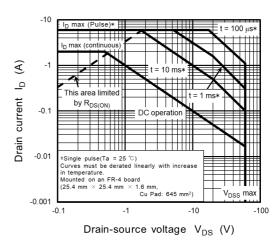


Fig. 9.12 Safe Operating Area



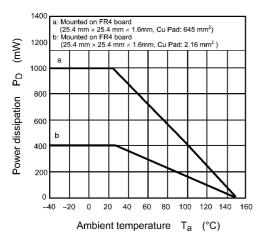


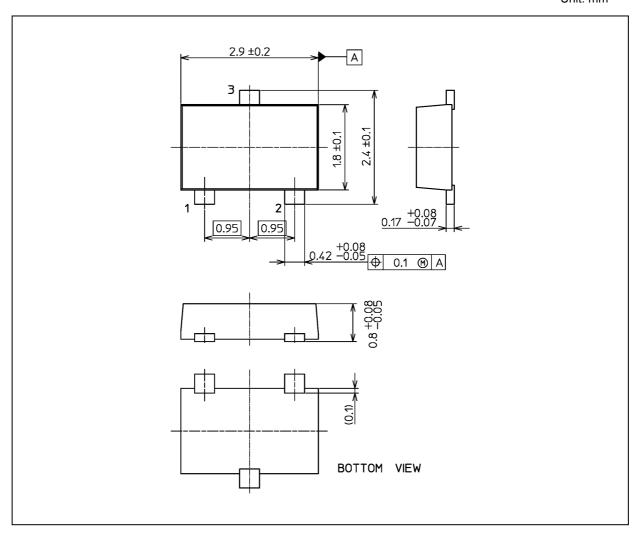
Fig. 9.13 P_D - T_a

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.011 g (typ.)

| | Package Name(s) |
|-------------------|-----------------|
| Nickname: SOT-23F | |



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